



Bipolar NPN Bare Die – BTN6005

Part Description

The BTN6005 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications. PNP Complement is BTP6005.

Key Parameters:

- VCBO = 40V
- VCEO = 32V
- VEBO = 5V
- hFE = 68-470 @ VCE = 3V, IC = 0.1A
- VCE(Sat) = 0.4V @ IC = 0.5A, IB = 50mA
- fT = 50 MHz @ VCE = 5V, IE = 0A
- COBO = 20pF @ VCB = 10V

Features

Low VCE(sat). Designed to provide performance equivalent to ROHM 2SC2060

Die Size (Unsawn)

650µm X 650µm, 26 Mils X 26 Mils

This is a shortform datasheet only

For the full datasheet

Please contact sales@siliconsupplies.com

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